



Product Change Notification



Product Group: Vishay Siliconix/ May 19, 2016/PCN SIL-0142016

Vishay Siliconix Announces Additional Copper Wire Conversion

DESCRIPTION OF CHANGE: As part of our continuous improvement package improvement program, Vishay Siliconix announces the qualification of Copper wire conversion on Low Voltage MOSFET part numbers **SI7456DP-T1-E3** and **SI7456DP-T1-GE3**.

CLASSIFICATION OF CHANGE: Material set conversion

REASON FOR CHANGE: Part of continued quality improvement program.

EXPECTED INFLUENCE ON QUALITY/RELIABILITY/PERFORMANCE: Enhancement to long-term product reliability. No changes will be made to electrical performance or datasheet parameters.

PRODUCT Category: Power MOSFETs

PART NUMBERS/SERIES/FAMILIES AFFECTED:

SI7456DP-T1-E3

SI7456DP-T1-GE3

VISHAY BRAND(s): Vishay Siliconix

TIME SCHEDULE: Shipments will begin in August 2016.

SAMPLE AVAILABILITY: Please contact your regional Vishay Sales office for sample availability.

PRODUCT IDENTIFICATION: There will be no change to part numbering. Products converted to Copper wire will have a datecode **W66Cxx** or later.

This PCN is considered approved, without further notification, unless we receive specific customer concerns before August 19, 2016 as specified by contract.

ISSUED BY: Dave MacDonald, Vishay Siliconix, Senior Manager, Technical Marketing

E-mail address: Dave.macdonald@Vishay.com

For further information, please contact your regional Vishay office.

The Americas

Vishay Siliconix
2201 Laurelwood Road
Santa Clara, Ca 95054
T: 408-567-8500
F: 408-567-8942

Europe

Vishay Electronic GmbH
Dr.-Felix-Zandman-Platz 1
D-95100
Selb, Germany
T: 49-9287-71 0
F: 49-9287-70435

Asia

Vishay Intertechnology Asia Pte. Ltd
25 Tampines Street 92
#02-00 Keppel Building
Singapore 528877
T: 65-6788-6668
F: 65-6788-0988

Vishay Intertechnology, Inc.

Corporate Headquarters 63 Lincoln Highway, Malvern, PA 19355-2143 U.S.A. Phone (610) 644-1300 Fax (610) 296-0657 www.vishay.com

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